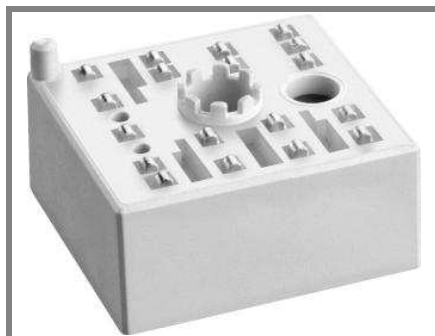




MiniSKiiP[®]0

3-phase bridge rectifier +
3-phase bridge inverter

SKiiP 03NAC126V1

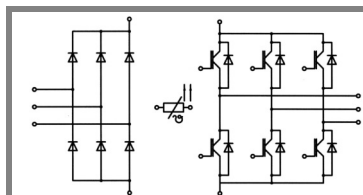
Preliminary Data

Features

- Fast Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections

Remarks

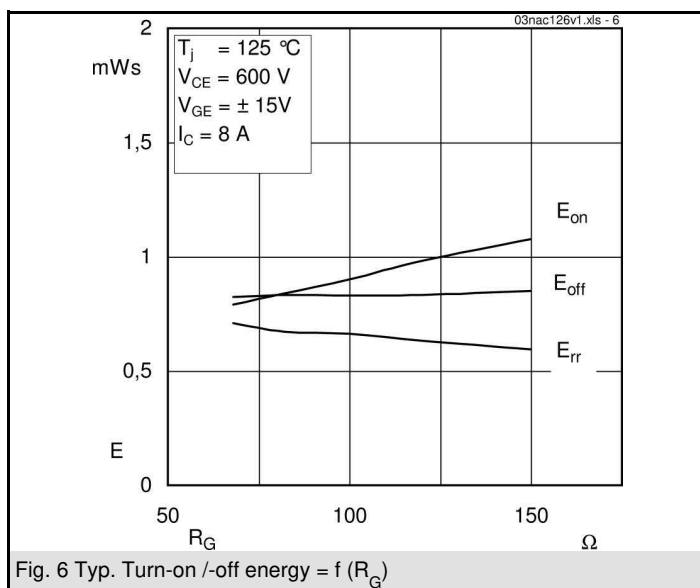
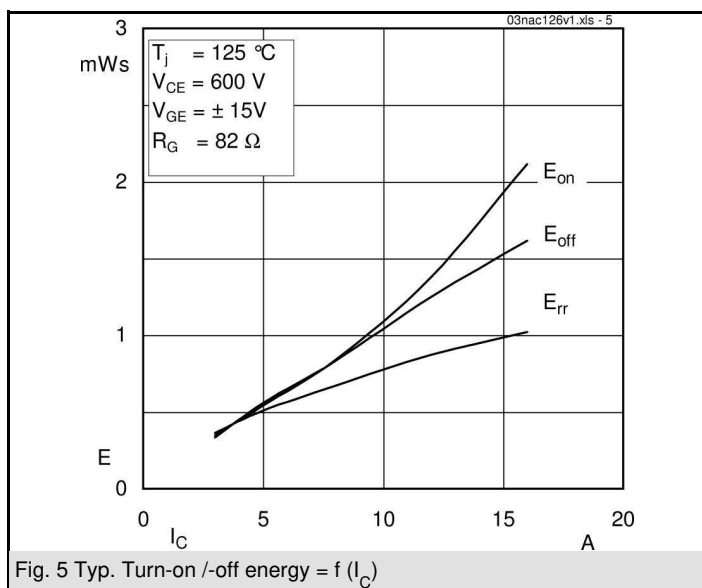
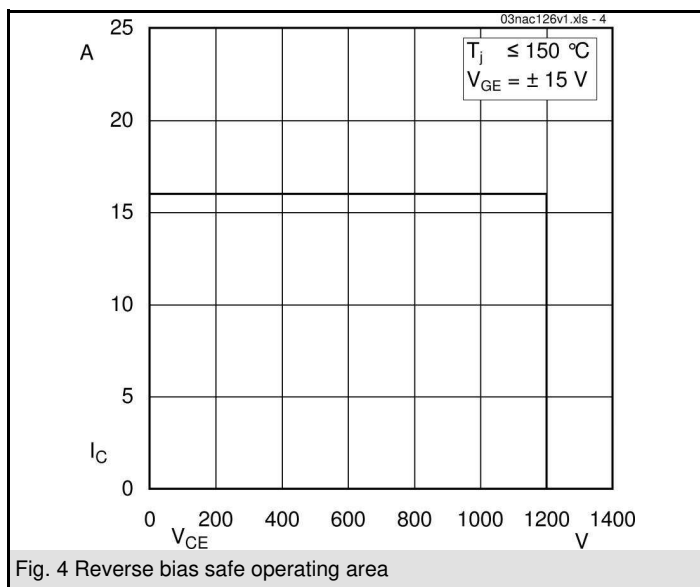
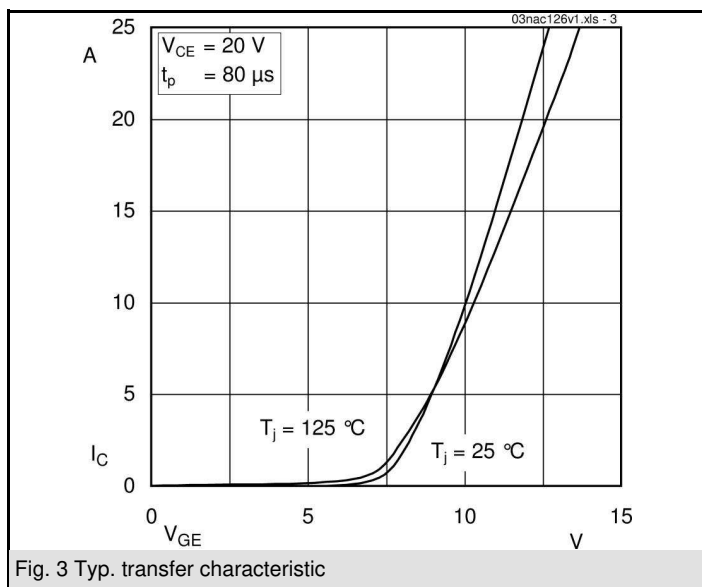
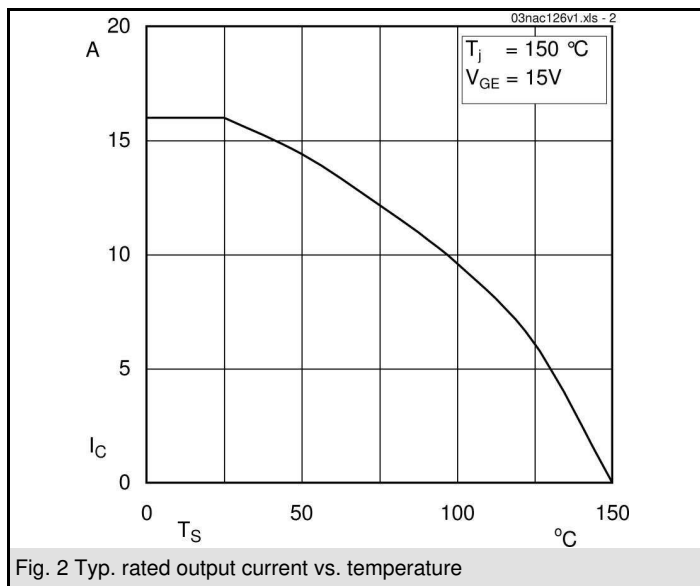
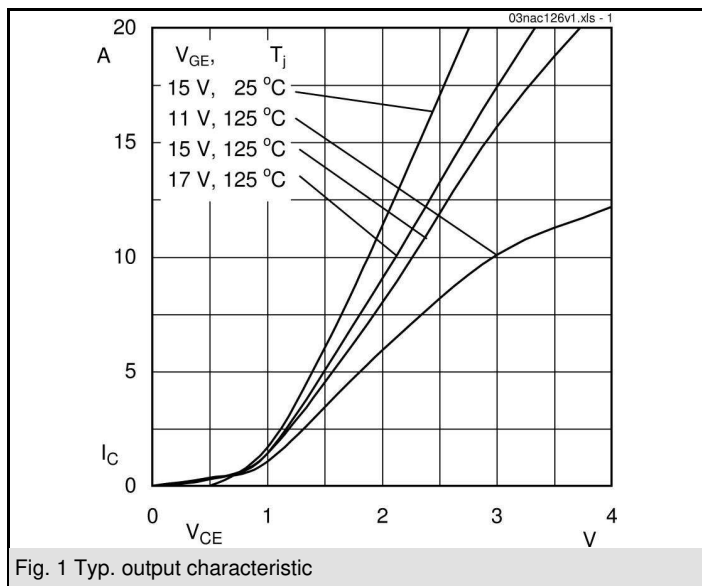
- V_{CEsat} , V_F = chip level value
- The Temp. Sensor has no basic insulation to the main circuit. The existing functional insulation allows a maximum potential difference of 850V to -DC.

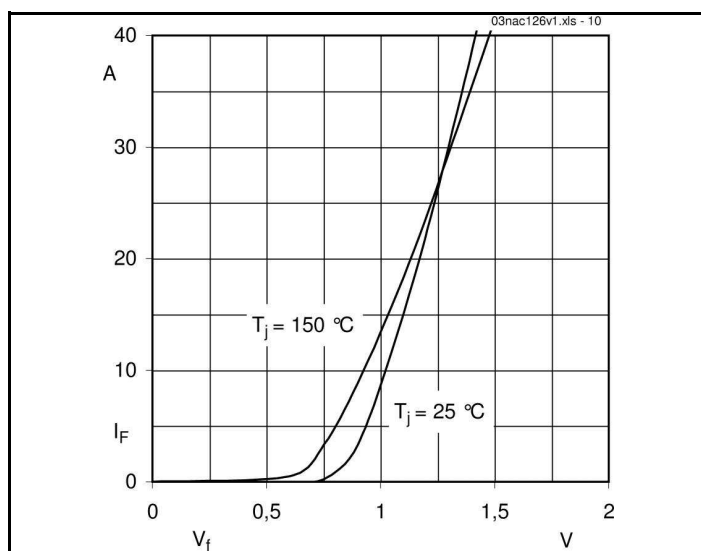
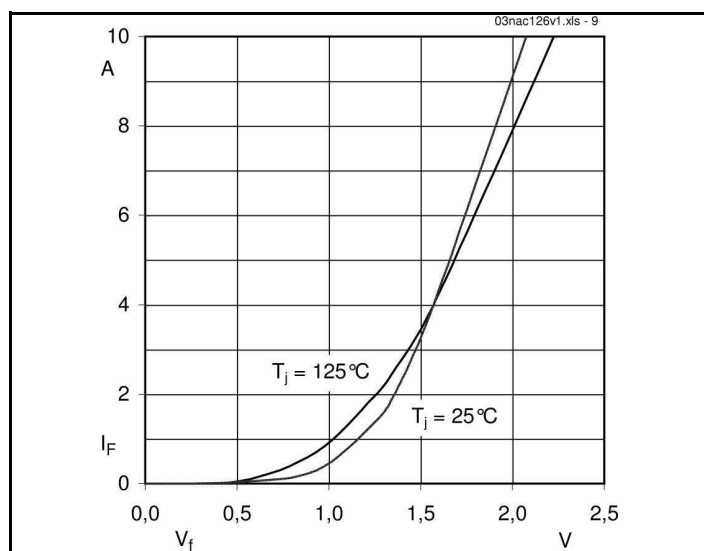
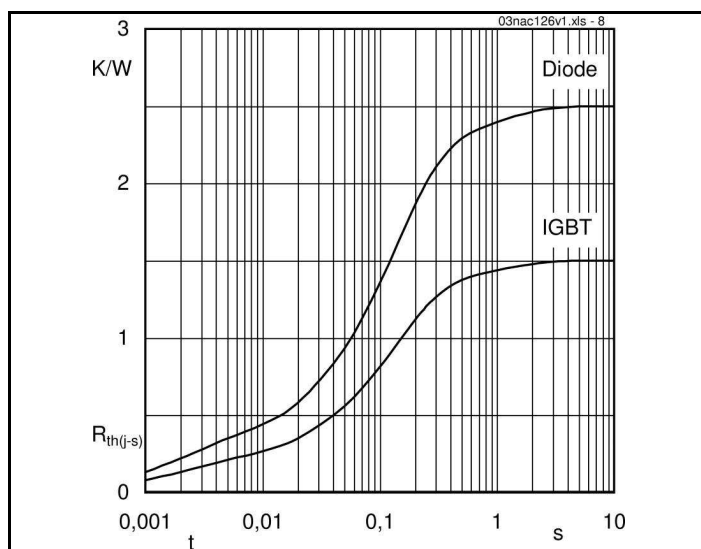
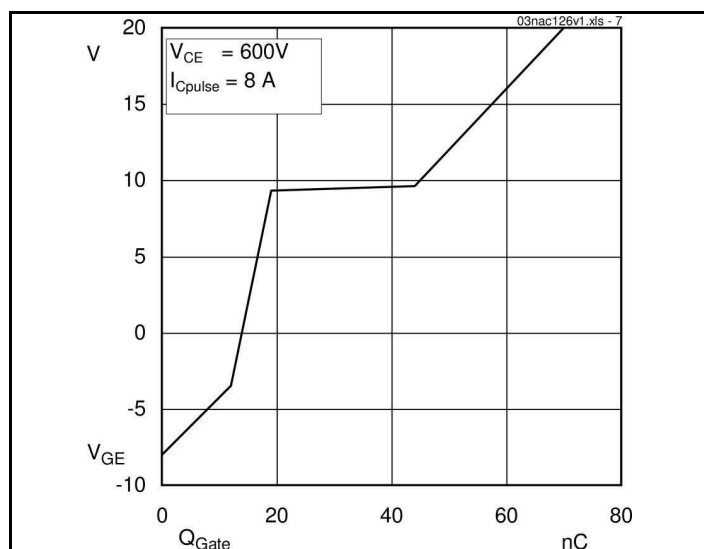


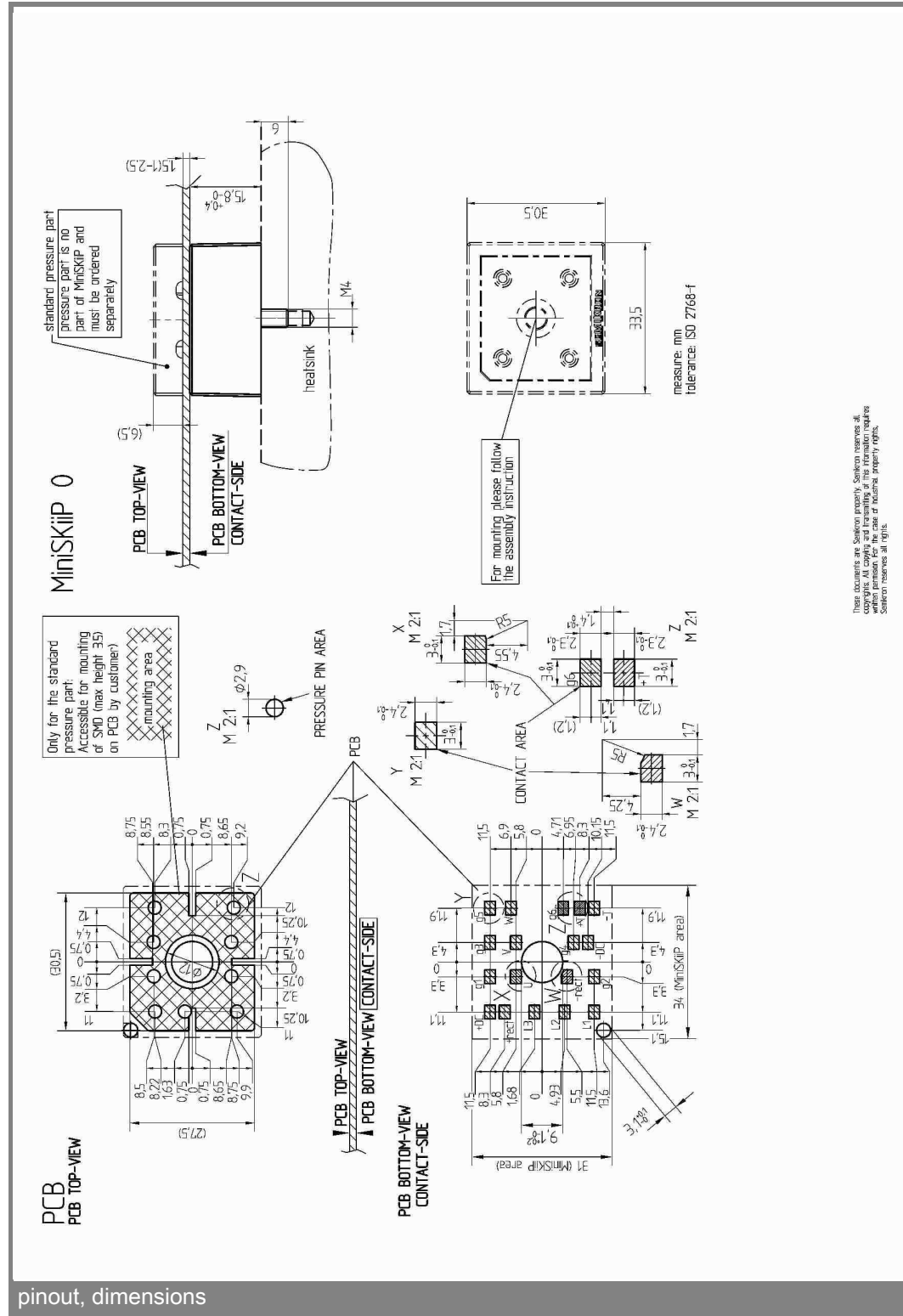
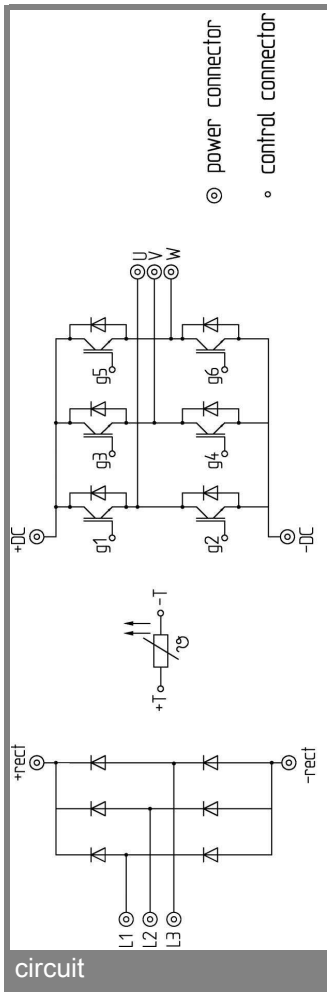
NAC

Absolute Maximum Ratings		T _S = 25 °C, unless otherwise specified		
Symbol	Conditions	Values	Units	
IGBT - Inverter				
V _{CES}	T _s = 25 (70) °C	1200	V	
I _C		16 (15)	A	
I _{CRM}		16	A	
V _{GES}		± 20	V	
T _j		-40...+150	°C	
Diode - Inverter				
I _F	T _s = 25 (70) °C	14 (11)	A	
I _{FRM}		16	A	
T _j		-40...+150	°C	
Diode - Rectifier				
V _{RRM}	T _s = 70 °C	1600	V	
I _F		35	A	
I _{FSM}		t _p = 10 ms, sin 180 °, T _j = 25 °C	220	A
i ² t		t _p = 10 ms, sin 180 °, T _j = 25 °C	240	A²s
T _j		-40...+150	°C	
Module				
I _{tRMS}	per power terminal (20 A / spring)	20	A	
T _{stg}		-40...+125	°C	
V _{isol}	AC, 1 min.	2500	V	

Characteristics		$T_S = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT - Inverter					
V_{CEsat}	$I_{Cnom} = 8\text{ A}$, $T_j = 25\text{ (125) °C}$		1,7 (2)	2,1 (2,4)	V
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 0,3\text{ mA}$	5	5,8	6,5	V
$V_{CE(TO)}$	$T_j = 25\text{ (125) °C}$		1 (0,9)	1,2 (1,1)	V
r_T	$T_j = 25\text{ (125) °C}$		87 (138)	113 (162)	mΩ
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		0,7		nF
C_{oes}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		0,1		nF
C_{res}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		0,1		nF
$R_{th(j-s)}$	per IGBT		1,5		K/W
$t_{d(on)}$	under following conditions		40		ns
t_r	$V_{CC} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$		25		ns
$t_{d(off)}$	$I_{Cnom} = 8\text{ A}$, $T_j = 125\text{ °C}$		370		ns
t_f	$R_{Gon} = R_{Goff} = 82\text{ Ω}$		85		ns
E_{on}	inductive load		0,9		mJ
E_{off}			0,9		mJ
Diode - Inverter					
$V_F = V_{EC}$	$I_{Fnom} = 8\text{ A}$, $T_j = 25\text{ (125) °C}$		1,9 (2)	2,2 (2,4)	V
$V_{(TO)}$	$T_j = 25\text{ (125) °C}$		1 (0,8)	1,1 (0,9)	V
r_T	$T_j = 25\text{ (125) °C}$		112 (150)	138 (187)	mΩ
$R_{th(j-s)}$	per diode		2,5		K/W
I_{RRM}	under following conditions		13		A
Q_{rr}	$I_{Fnom} = 8\text{ A}$, $V_R = 600\text{ V}$		1,6		μC
E_{rr}	$V_{GE} = 0\text{ V}$, $T_j = 125\text{ °C}$		0,7		mJ
	$di_F/dt = 480\text{ A/μs}$				
Diode - Rectifier					
V_F	$I_{Fnom} = 15\text{ A}$, $T_j = 25\text{ °C}$		1,1		V
$V_{(TO)}$	$T_j = 150\text{ °C}$		0,8		V
r_T	$T_j = 150\text{ °C}$		20		mΩ
$R_{th(j-s)}$	per diode		1,5		K/W
Temperature Sensor					
R_{ts}	3 %, $T_r = 25\text{ (100) °C}$		1000(1670)		Ω
Mechanical Data					
w			21,5		g
M_s	Mounting torque	2		2,5	Nm







This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.